

## FNK N-Channel Enhancement Mode Power MOSFET

### Description

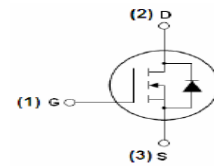
The FNK01N15T uses advanced trench Technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge .It can be used in a wide variety of applications

### General Features

- $V_{DS} = 100V, I_D = 150A$   
 $R_{DS(ON)} < 5.7m\Omega @ V_{GS}=10V$
- High density cell design for ultra low  $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation
- Good stability and uniformity with high EAS

### Application

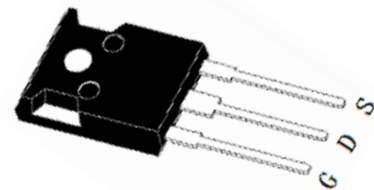
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



Marking and pin Assignment



TO-263 top view

### PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
FNK01N15T	FNK01N15T	TO-247	-	-	-

### ABSOLUTE MAXIMUM RATINGS( $T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	$I_D(25^{\circ}C)$	150	A
	$I_{DM}$	600	A
Maximum Power Dissipation	$P_D$	375	W
Single pulse avalanche energy(Note 5)	EAS	433	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^{\circ}C$

## THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	0.4	$^{\circ}\text{C/W}$
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## ELECTRICAL CHARACTERISTICS (TA=25 $^{\circ}\text{C}$ unless otherwise noted)

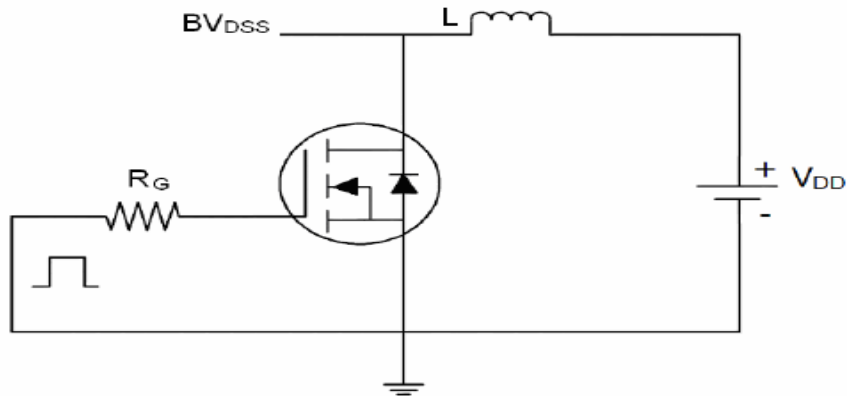
Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	100	110		V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2	2.8	4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A		5.0	5.7	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =20A	70			S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, F=1.0MHz		6470		PF
Output Capacitance	C <sub>oss</sub>			690		PF
Reverse Transfer Capacitance	C <sub>rss</sub>			430		PF
SWITCHING CHARACTERISTICS (Note 4)						
Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =50V, V <sub>GS</sub> =10V, R <sub>GEN</sub> =3Ω I <sub>D</sub> =2A RL=2.5Ω		28		nS
Turn-on Rise Time	t <sub>r</sub>			22		nS
Turn-Off Delay Time	t <sub>d(off)</sub>			43.5		nS
Turn-Off Fall Time	t <sub>f</sub>			14.5		nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =50V, I <sub>D</sub> =20A, V <sub>GS</sub> =10V		139		nC
Gate-Source Charge	Q <sub>gs</sub>			34		nC
Gate-Drain Charge	Q <sub>gd</sub>			56		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A		0.85	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>				160	A
Reverse Recovery Time	trr	TJ = 25℃, IF = 20A		60	90	nS
Reverse Recovery Charge	Qrr	di/dt = 500A/us(Note3)		177	200	nC

## NOTES:

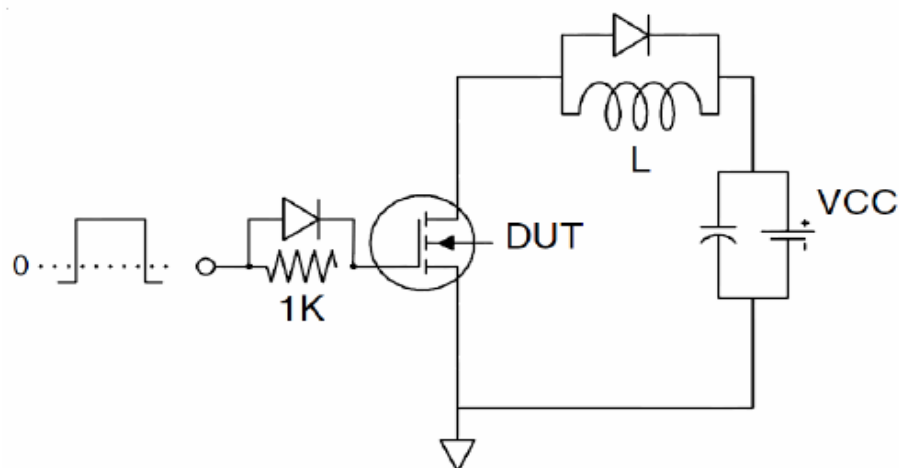
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on 1in<sup>2</sup> FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production testing
5. EAS condation:  $T_J=25^{\circ}\text{C}$ ,  $V_{dd}=20V$ ,  $V_g=10V$ ,  $L=0.5mH$ ,  $R_g=25\Omega$

## Test circuit

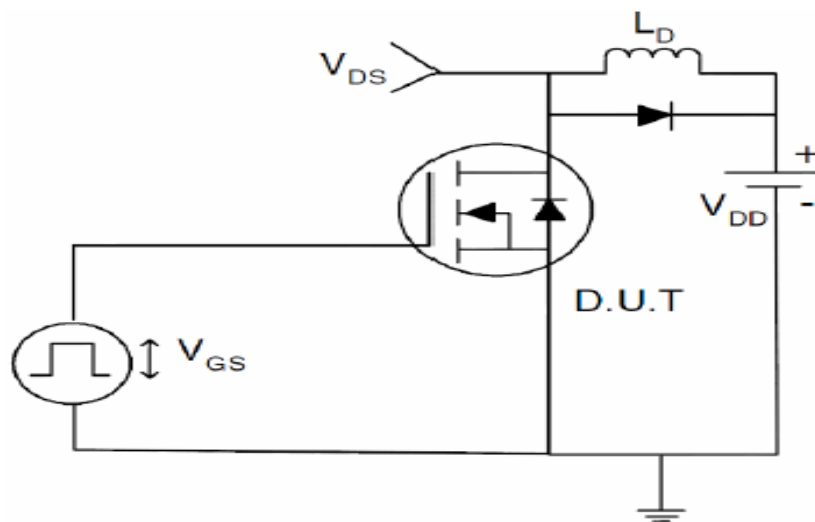
### 1) EAS Test Circuit



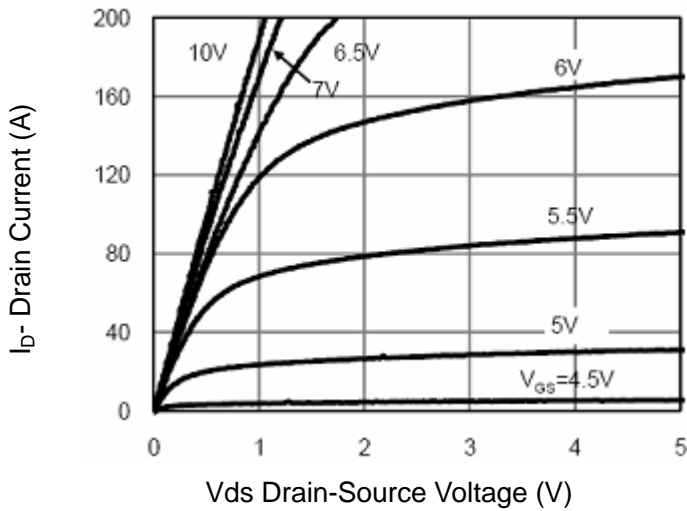
### 2) Gate Charge Test Circuit



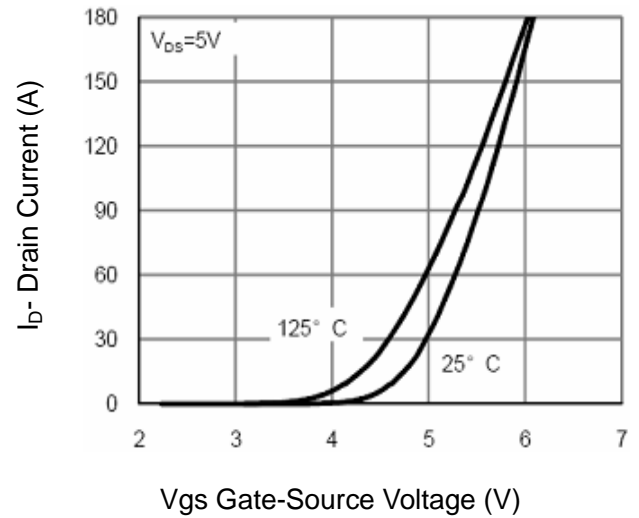
### 3) Switch Time Test Circuit



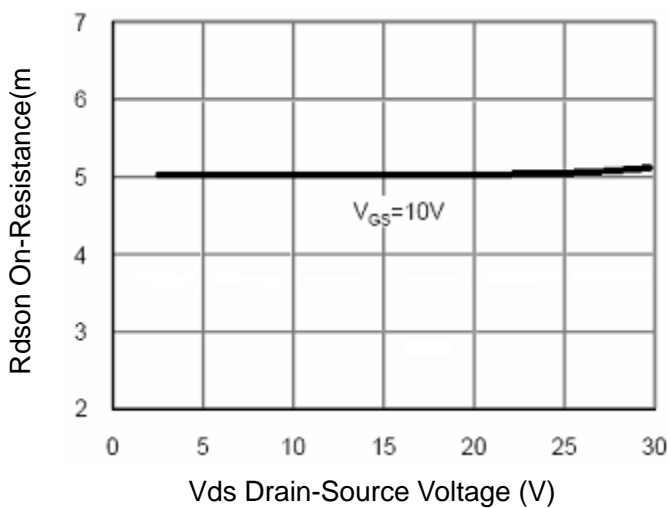
## Typical Electrical and Thermal Characteristics (Curves)



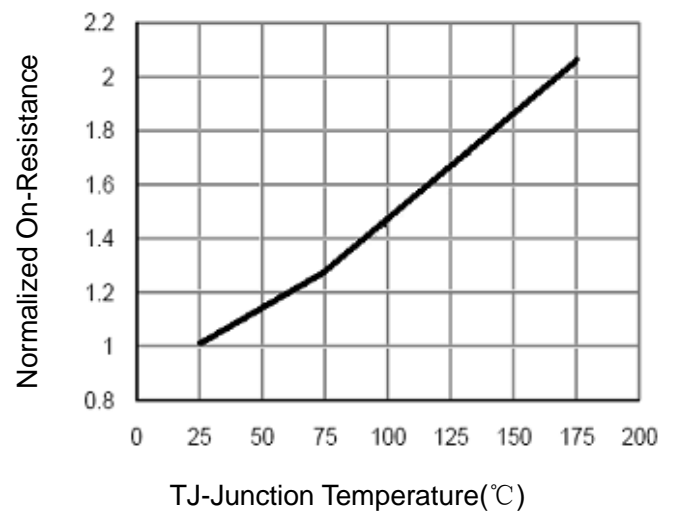
**Figure 1 Output Characteristics**



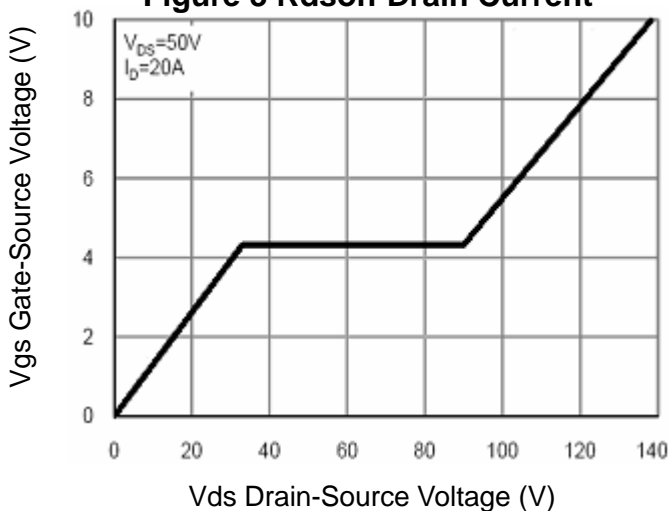
**Figure 2 Transfer Characteristics**



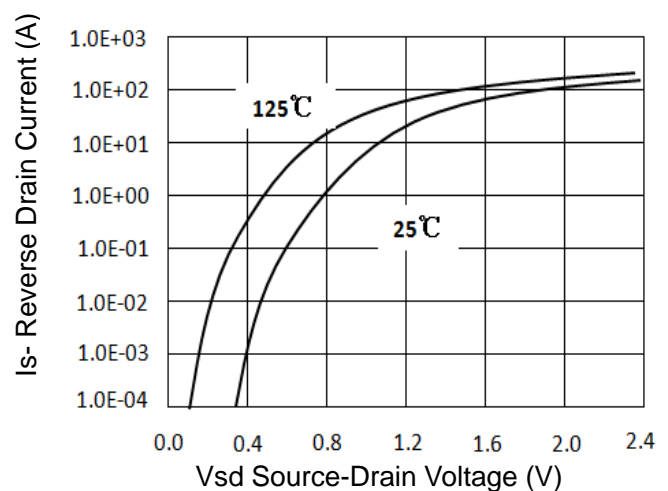
**Figure 3  $R_{DS(on)}$ -Drain Current**



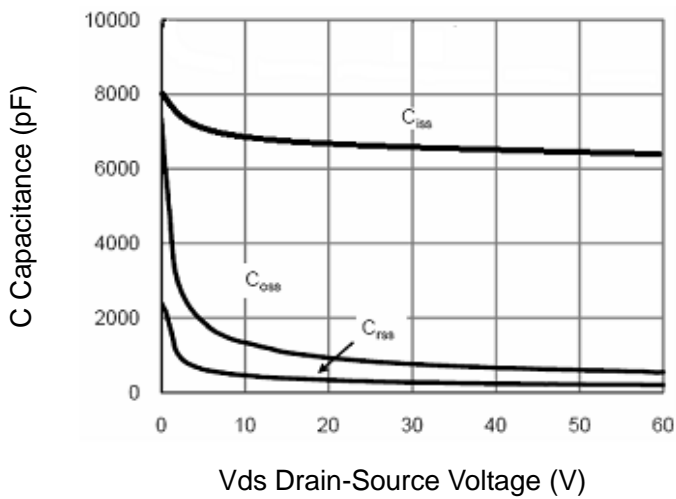
**Figure 4  $R_{DS(on)}$ -Junction Temperature**



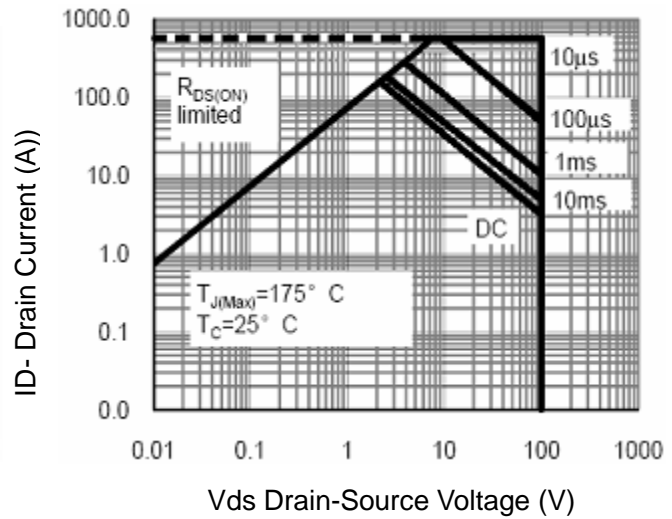
**Figure 5 Output CHARACTERISTICS**



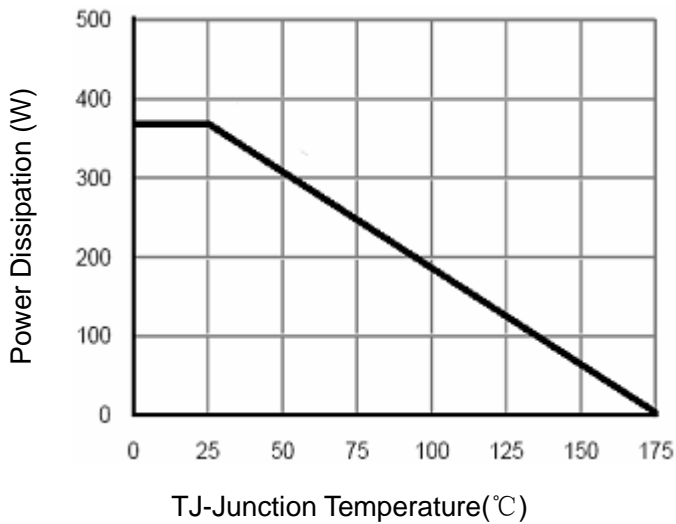
**Figure 6 Source- Drain Diode Forward**



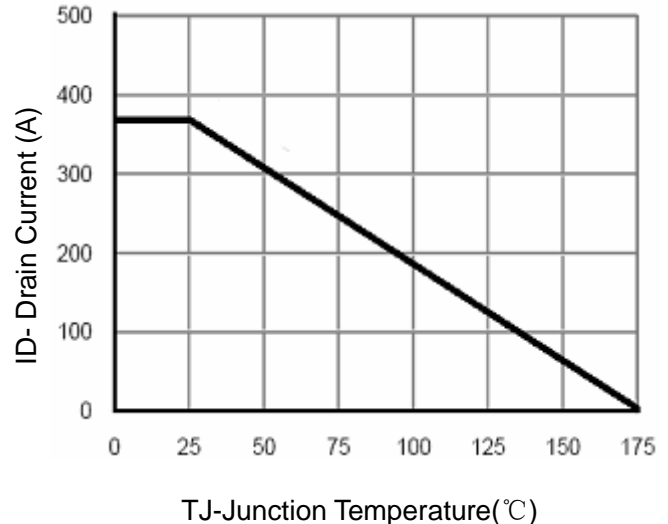
**Figure 7 Capacitance vs Vds**



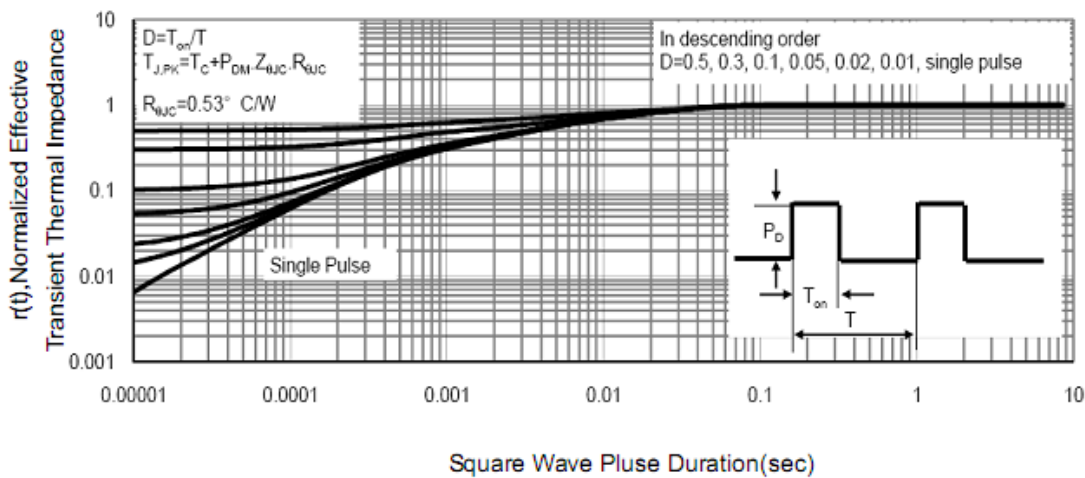
**Figure 8 Safe Operation Area**



**Figure 9 Power De-rating**

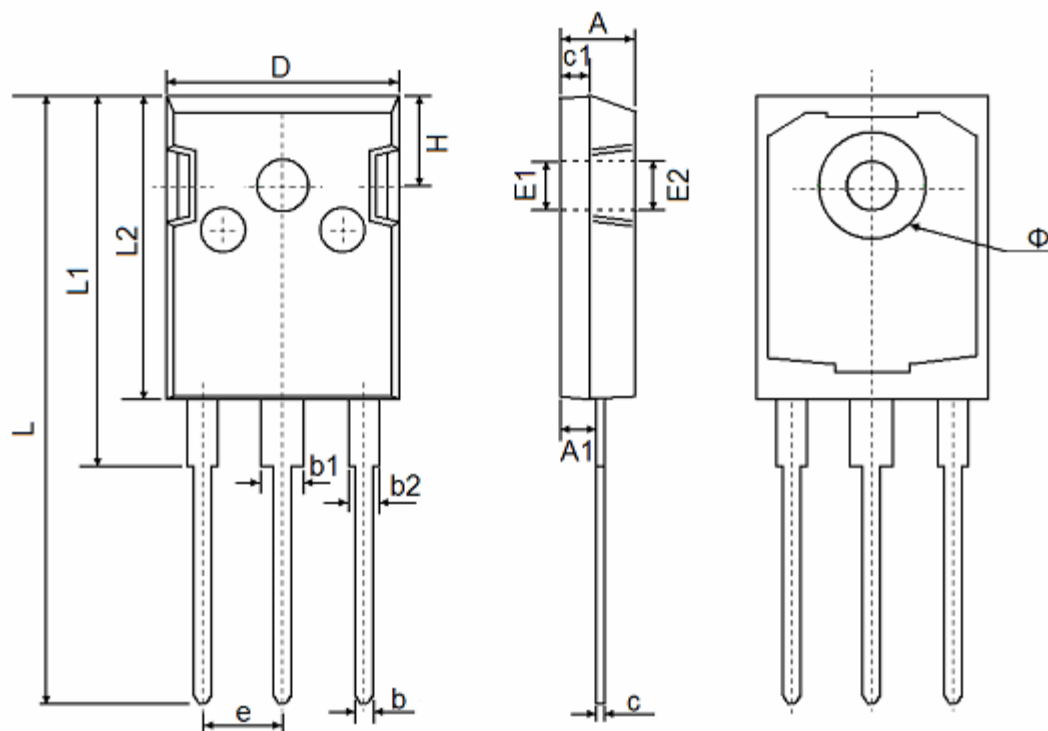


**Figure 10 Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

## TO-247 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF		0.138 REF	
E2	3.600 REF		0.142 REF	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP		0.215 TYP	
H	5.980 REF		0.235 REF	

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